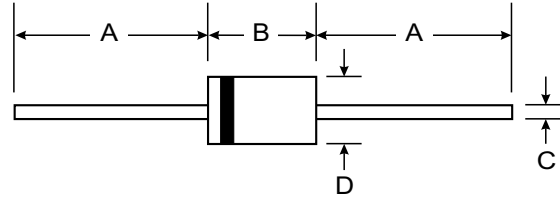


Features

- High switching speed: max. 4 ns
- Reverse voltage: max. 25V , 50V
- Peak reverse voltage: max. 35V, 75 V
- Pb / RoHS Free



Mechanical Data

- Case: DO-35 Glass Case
- Weight: approx. 0.13g

DO-35		
Dim	Min	Max
A	25.40	—
B	—	4.00
C	—	0.60
D	—	2.00
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

Parameter			Symbol	Value			Unit	
Maximum Peak Reverse Voltage		BAW75	V_{RM}	25			V	
		BAW76		50				
Maximum Reverse Voltage		BAW75	V_{RM}	35			V	
		BAW76		75				
Maximum Average Forward Current Half Wave Rectication with Resistive Load , f ≥ 50Hz			$I_{F(AV)}$	150 ⁽¹⁾			mA	
Maximum Power Dissipation			P_D	500 ⁽¹⁾			mW	
Maximum Surge Forward Current at t < 1μs , Tj = 25 °C			I_{FSM}	2			A	
Maximum Junction Temperature			T_J	200			°C	
Storage Temperature Range J			T_S	-65 to + 200			°C	
Parameter		Symbol	Test Condition		Min	Typ	Max	Unit
Reverse Current	BAW75	I_R	$V_R = 25\text{ V}$		-	-	100	nA
	BAW76		$V_R = 50\text{ V}$		-	-	100	
Forward Voltage	BAW75	V_F	$I_F = 30\text{ mA}$		-	-	1.0	V
	BAW76		$I_F = 100\text{ mA}$		-	-	1.0	
Reverse Breakdown Voltage	BAW75	$V_{(BR)R}$	Test with 5μA pulses		35	-	-	V
	BAW76				75	-	-	
Diode Capacitance	BAW75	Cd	f = 1MHz ; $V_R = 0$		-	-	4.0	pF
	BAW76				-	-	2.0	
Reverse Recovery Time		Trr	$I_F = 10\text{ mA}$, $I_R = 10\text{ mA}$ Irr = 1mA		-	-	4	ns

Note : (1) Valid provided that leads are kept at ambient temperature at a distance of 8mm from case.

**FIG. 1 ADMISSIBLE POWER DISSIPATION
VERSUS AMBIENT TEMPERATURE**

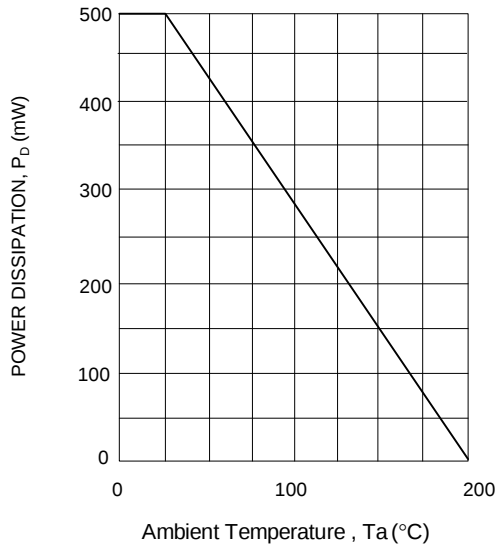
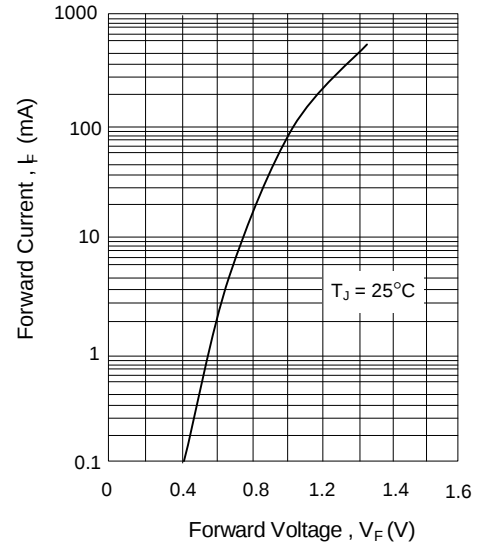
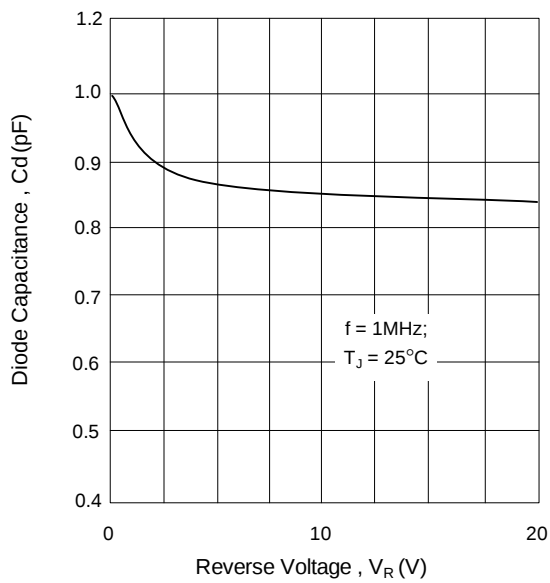


FIG. 2 TYPICAL FORWARD VOLTAGE



**FIG. 3 TYPICAL DIODE CAPACITANCE AS
A FUNCTION OF REVERSE VOLTAGE**



**FIG. 4 TYPICAL REVERSE CURRENT
VERSUS JUNCTION TEMPERATURE**

